

SWITCHING P-CHANNEL POWER MOSFET

DESCRIPTION

The 2SJ687 is P-channel MOSFET device and a excellent switch that can be driven by a low power-supply voltage.

FEATURES

- Low on-state resistance
 $R_{DS(on)1} = 7.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -10 \text{ A)}$
 $R_{DS(on)2} = 9.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = -3.0 \text{ V, } I_D = -10 \text{ A)}$
 $R_{DS(on)3} = 20 \text{ m}\Omega \text{ MAX. (} V_{GS} = -2.5 \text{ V, } I_D = -10 \text{ A)}$
- 2.5 V drive available
- Avalanche capability ratings

ORDERING INFORMATION

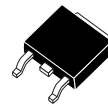
PART NUMBER	LEAD PLATING	PACKING	PACKAGE
2SJ687-ZK-E1-AY ^{Note}	Pure Sn (Tin)	Tape 2500 p/reel	TO-252 (MP-3ZK) 0.27 g TYP.
2SJ687-ZK-E2-AY ^{Note}			

Note Pb-free (This product does not contain Pb in external electrode.)

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±12	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±20	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±60	A
Total Power Dissipation (T _C = 25°C)	P _{T1}	36	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current ^{Note2}	I _{AS}	-20	A
Single Avalanche Energy ^{Note2}	E _{AS}	40	mJ

(TO-252)



Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Starting T_{ch} = 25°C, V_{DD} = -10 V, R_G = 25 Ω, V_{GS} = -12 → 0 V

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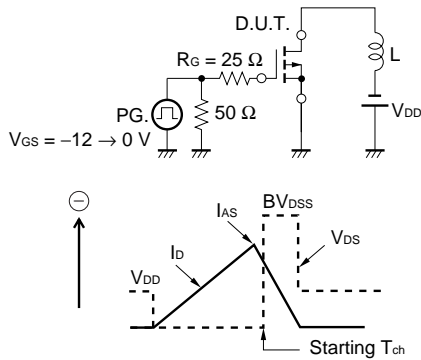
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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

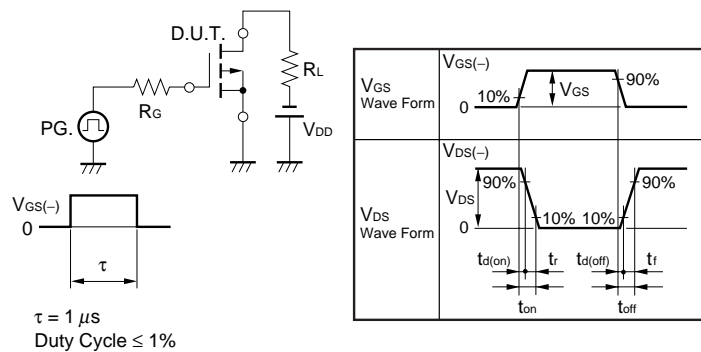
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V			±100	nA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-0.6	-1.2	-1.45	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = -10 V, I _D = -10 A	20			S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -10 A		5.4	7.0	mΩ
	R _{DS(on)2}	V _{GS} = -3.0 V, I _D = -10 A		7.1	9.0	mΩ
	R _{DS(on)3}	V _{GS} = -2.5 V, I _D = -10 A		10.8	20	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V,		4400		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V,		1070		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		760		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10 V, I _D = -10 A,		36		ns
Rise Time	t _r	V _{GS} = -4.5 V,		220		ns
Turn-off Delay Time	t _{d(off)}	R _G = 3 Ω		270		ns
Fall Time	t _f			310		ns
Total Gate Charge	Q _G	V _{DD} = -16 V,		57		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -4.5 V,		12		nC
Gate to Drain Charge	Q _{GD}	I _D = -20 A		28		nC
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = -20 A, V _{GS} = 0 V		0.85	1.5	V
Reverse Recovery Time	t _{rr}	I _F = -20 A, V _{GS} = 0 V,		200		ns
Reverse Recovery Charge	Q _{rr}	di/dt = -100 A/μs		240		nC

Note Pulsed

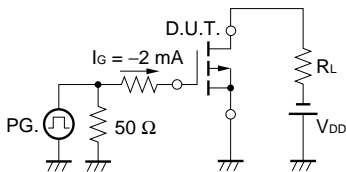
TEST CIRCUIT 1 AVALANCHE CAPABILITY



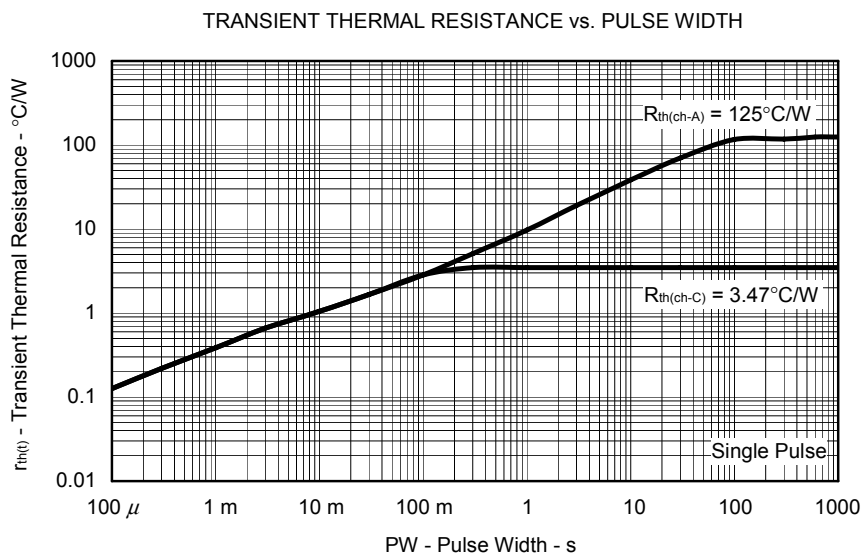
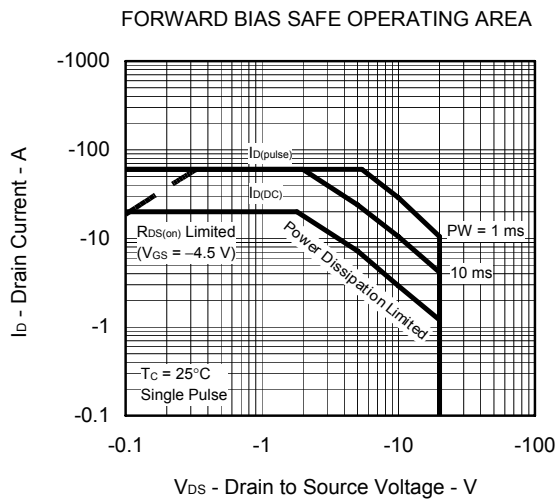
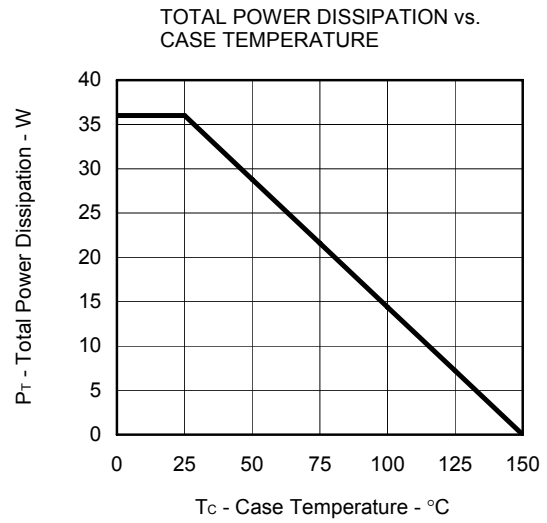
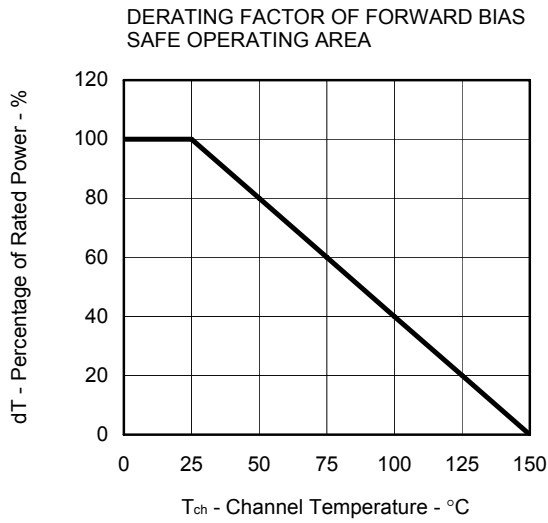
TEST CIRCUIT 2 SWITCHING TIME

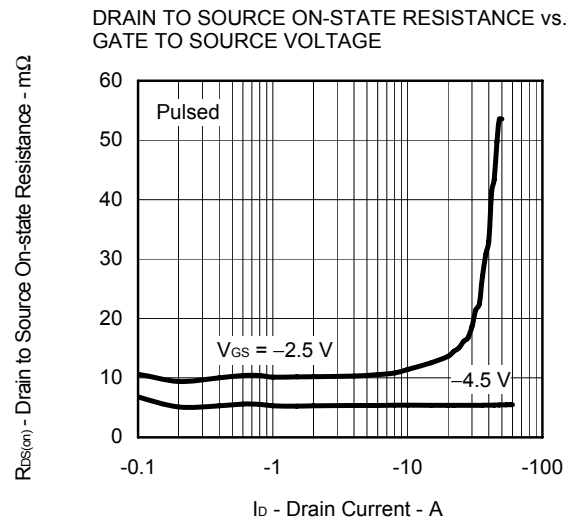
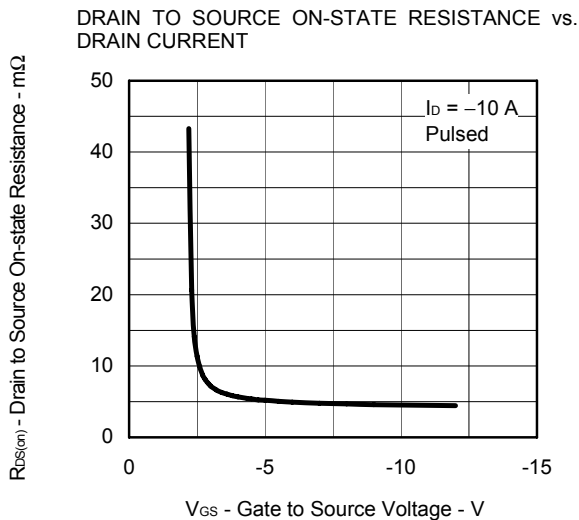
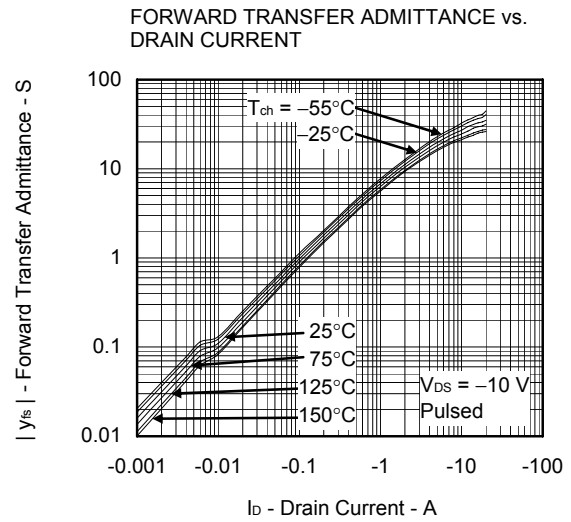
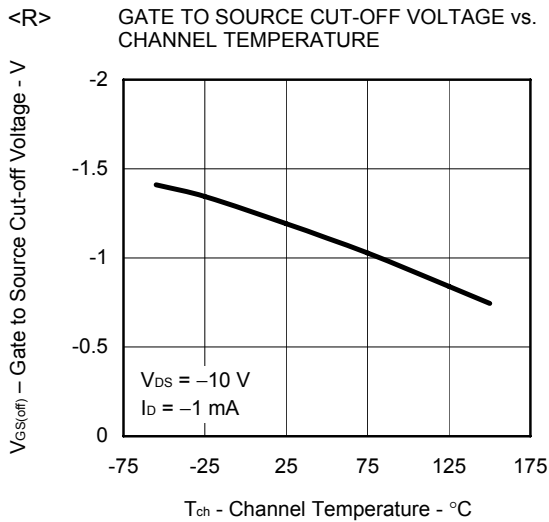
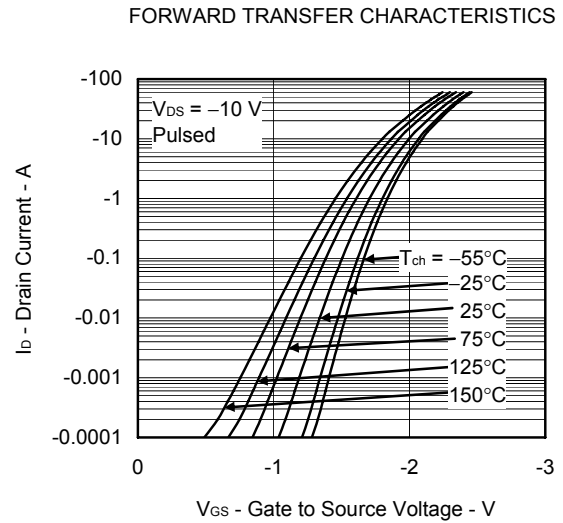
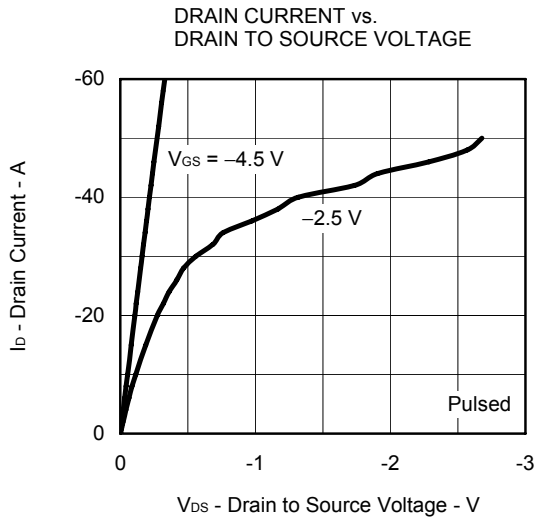


TEST CIRCUIT 3 GATE CHARGE

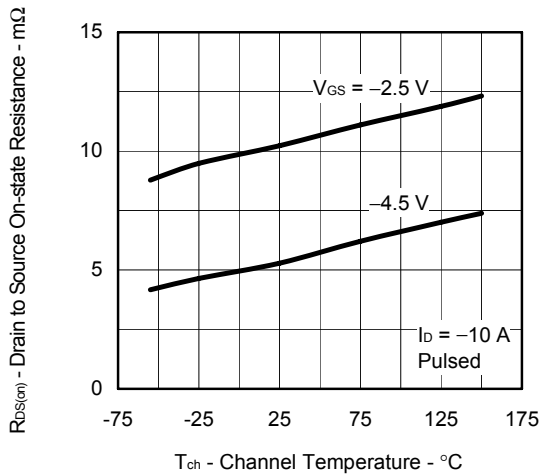


TYPICAL CHARACTERISTICS (T_A = 25°C)

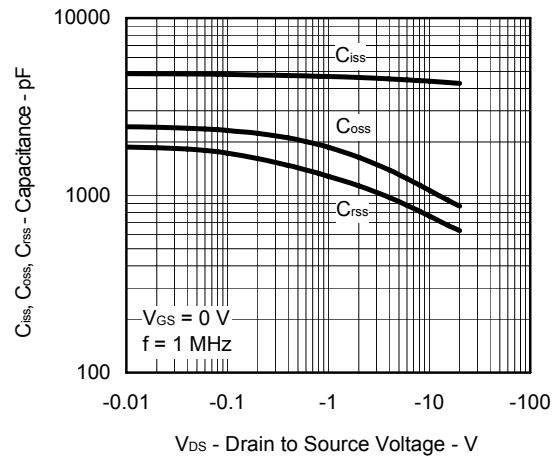




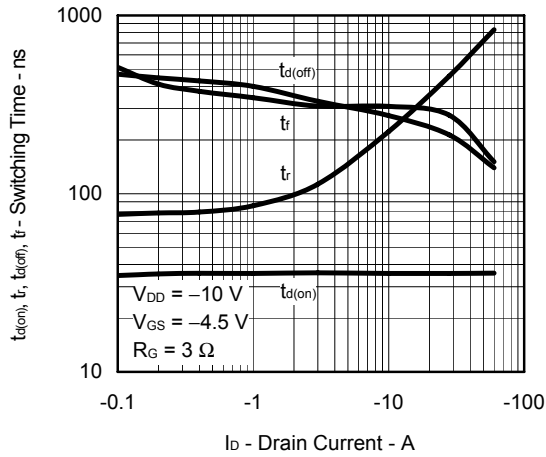
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



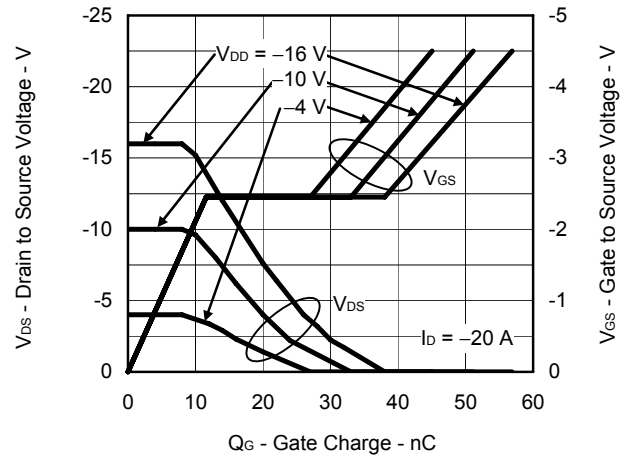
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



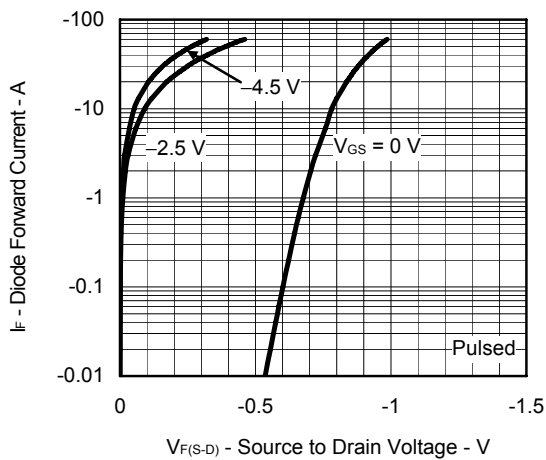
SWITCHING CHARACTERISTICS



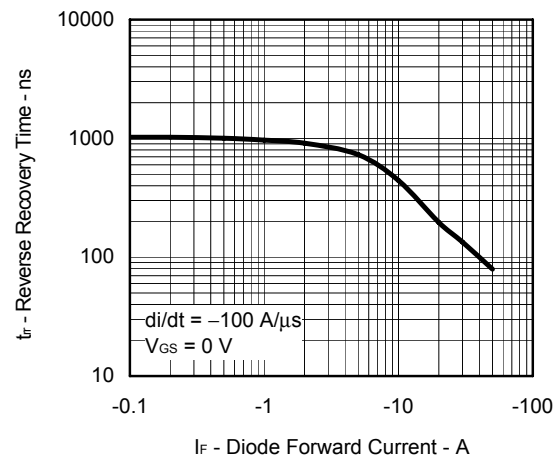
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



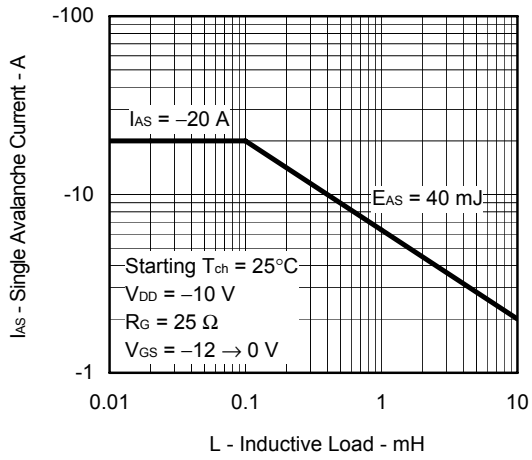
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



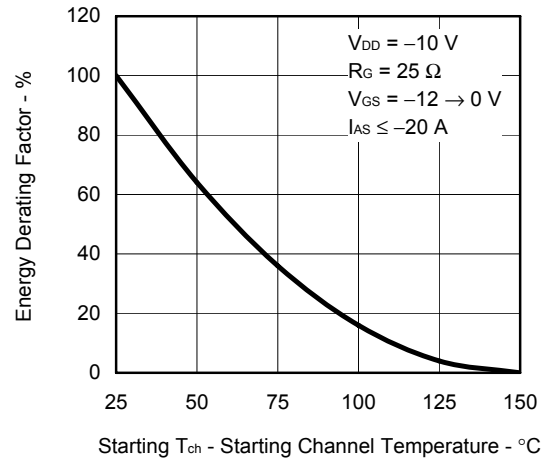
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

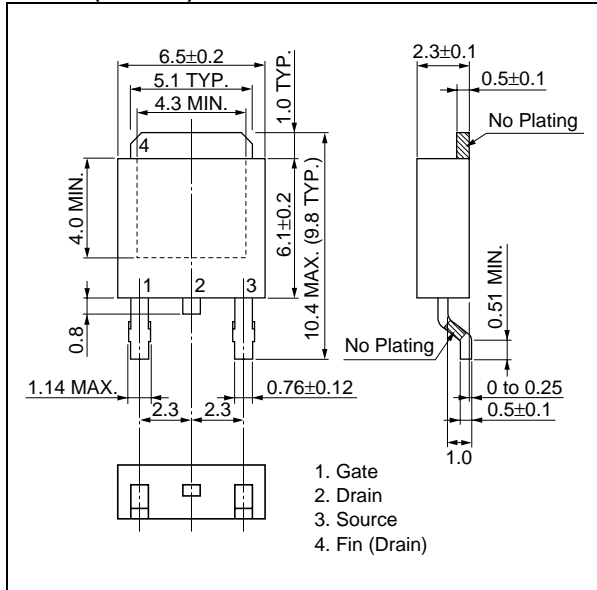


SINGLE AVALANCHE ENERGY DERATING FACTOR

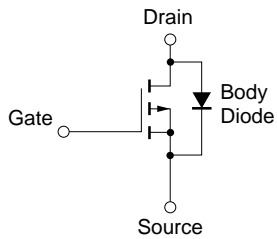


PACKAGE DRAWING (Unit: mm)

TO-252 (MP-3ZK)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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